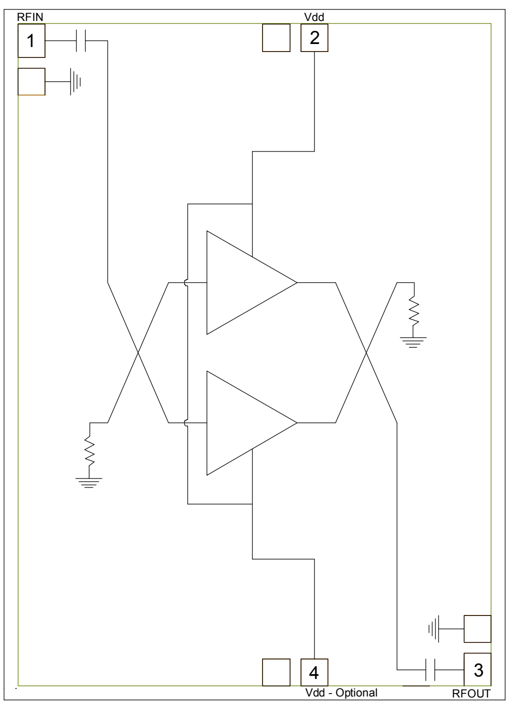
CMD222

5-11 GHz Balanced Low Noise Amplifier

Features

- ► Low noise figure
- ► High gain broadband performance
- ► Single positive supply voltage
- ► Bias top or bottom
- ► Small die size

Functional Block Diagram



Description

The CMD222 is a broadband MMIC low noise amplifier ideally suited for microwave radios and C and X-band applications where small size and low power consumption are needed. The broadband device delivers greater than 22 dB of gain with a corresponding output 1 dB compression point of +11 dBm and a noise figure of 1.2 dB. The CMD222 is a 50 ohm matched design eliminating the need for external DC blocks and RF port matching. The CMD222 offers full passivation for increased reliability and moisture protection.

Electrical Performance - V_{dd} = 4 V, T_A = 25 °C, F = 8 GHz

Parameter	Min	Typ	Max	Units
Frequency Range		5 - 11		GHz
Gain		22		dB
Noise Figure		1.2		dB
Input Return Loss		15		dB
Output Return Loss		14		dB
Output P1dB		11		dBm
Supply Current		107		mA

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Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, Vdd	5.5 V
RF Input Power	+23 dBm
Channel Temperature, Tch	150 °C
Power Dissipation, Pdiss	1.25 W
Thermal Resistance	52 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
Vdd	2.0	4.0	5.0	V
Idd		100		mA

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications - V_{dd} = 4 V, T_A = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range		5 - 11			7 - 9		GHz
Gain	17	22	25	19	22	25	dB
Noise Figure		1.4	2.3		1.2	1.6	dB
Input Return Loss		15			15		dB
Output Return Loss		13			13		dB
Output P1dB		11			11		dBm
Output IP3		23			23		dBm
Supply Current		107			107		mA
Gain Temperature Coefficient		0.013			0.013		dB/°C
Noise Figure Temperature Coefficient		0.007			0.007		dB/°C

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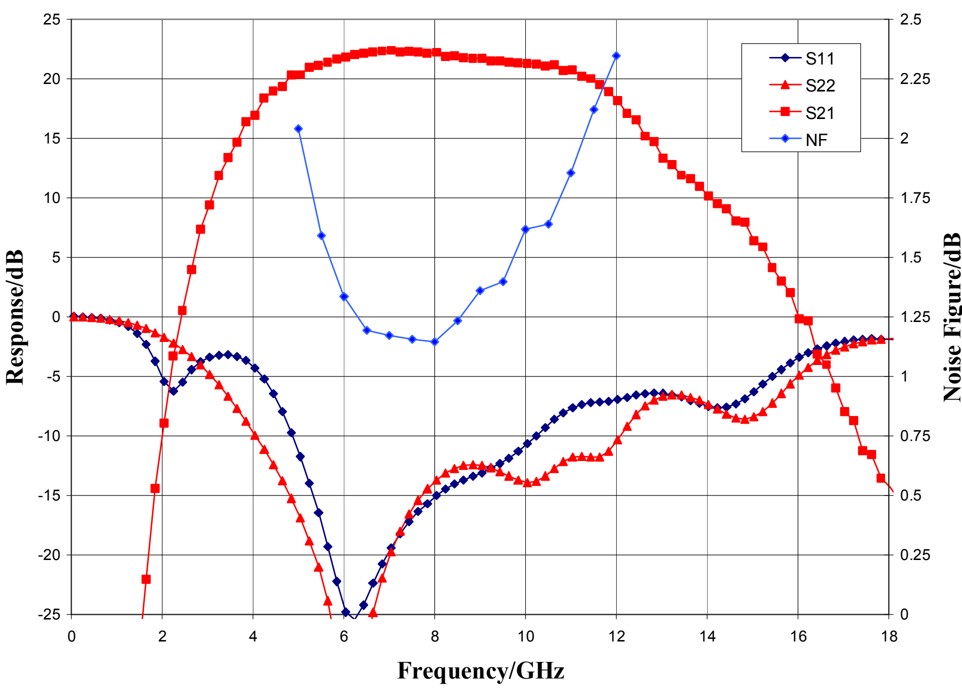
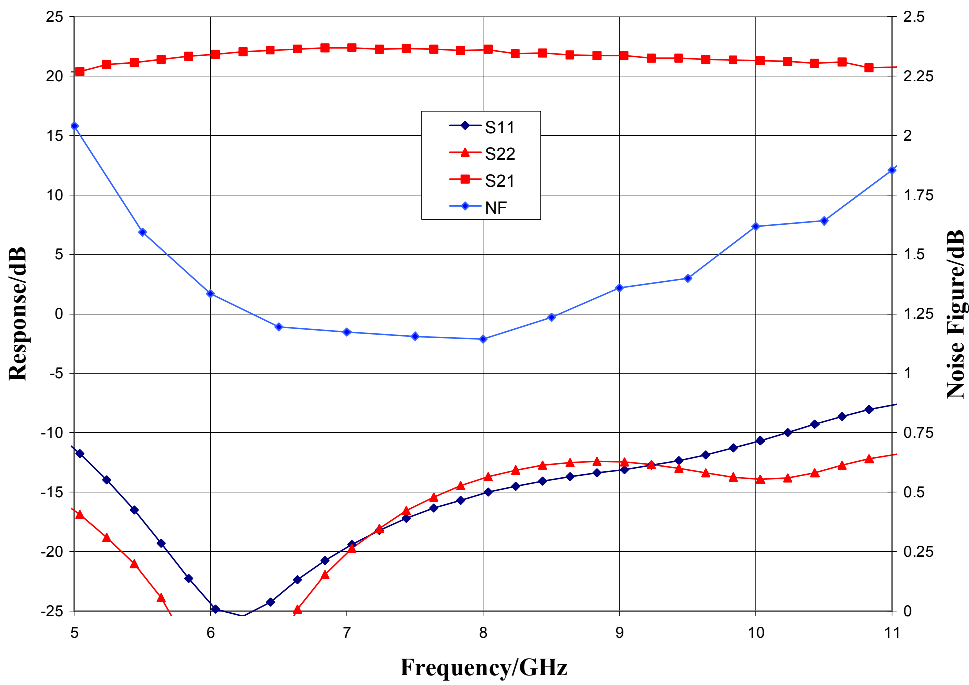
Typical Performance

Broadband Performance, V_{dd} = 4 V, I_{dd} = 107 mA, T_A = 25 °C



Narrow-band Performance, V_{dd} = 4 V, I_{dd} = 107 mA, T_A = 25 °C



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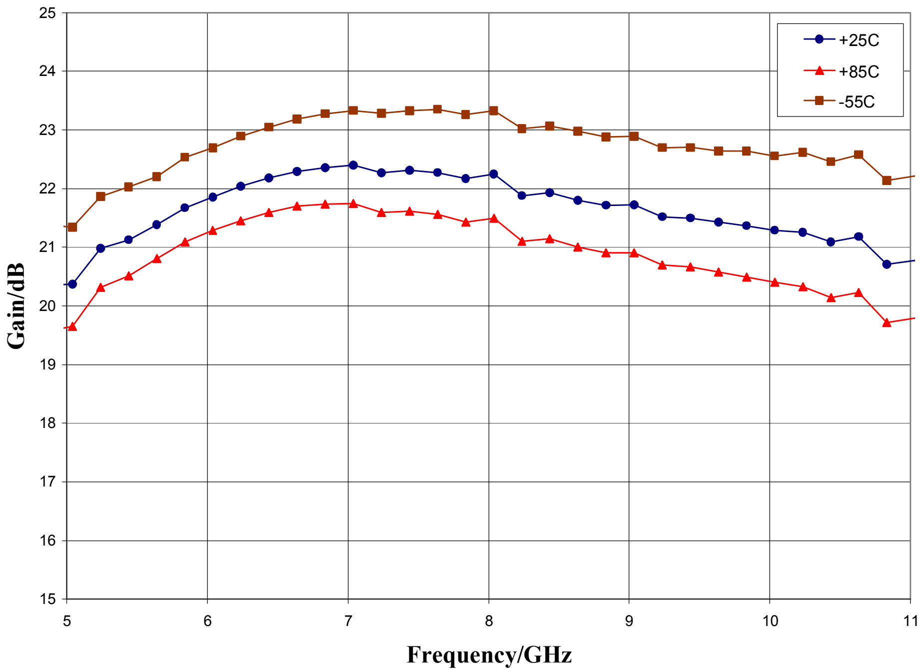
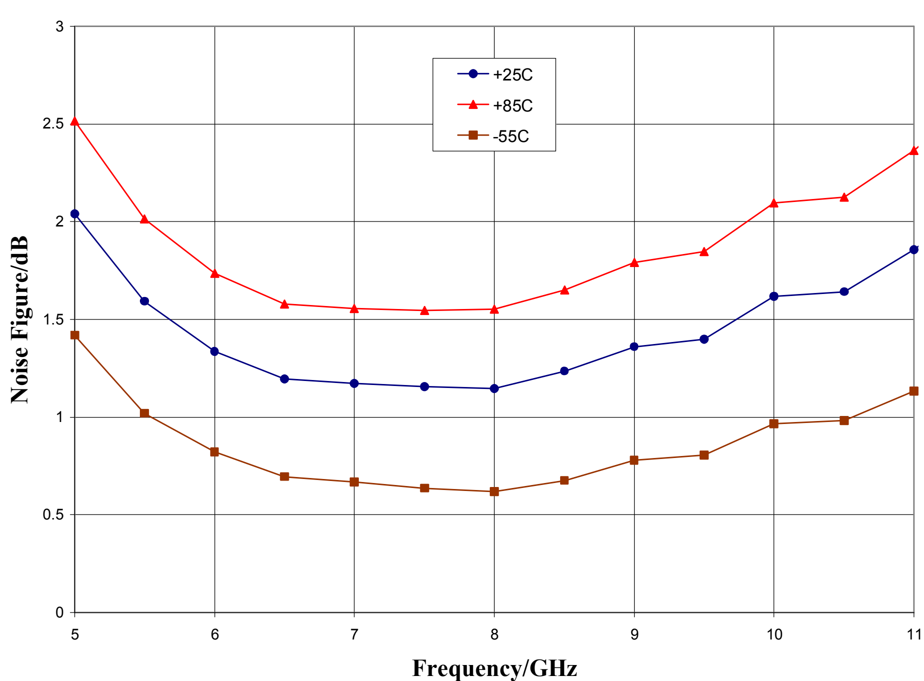
Typical Performance

Gain vs. Temperature, V_{dd} = 4 V



Noise Figure vs. Temperature, V_{dd} = 4 V



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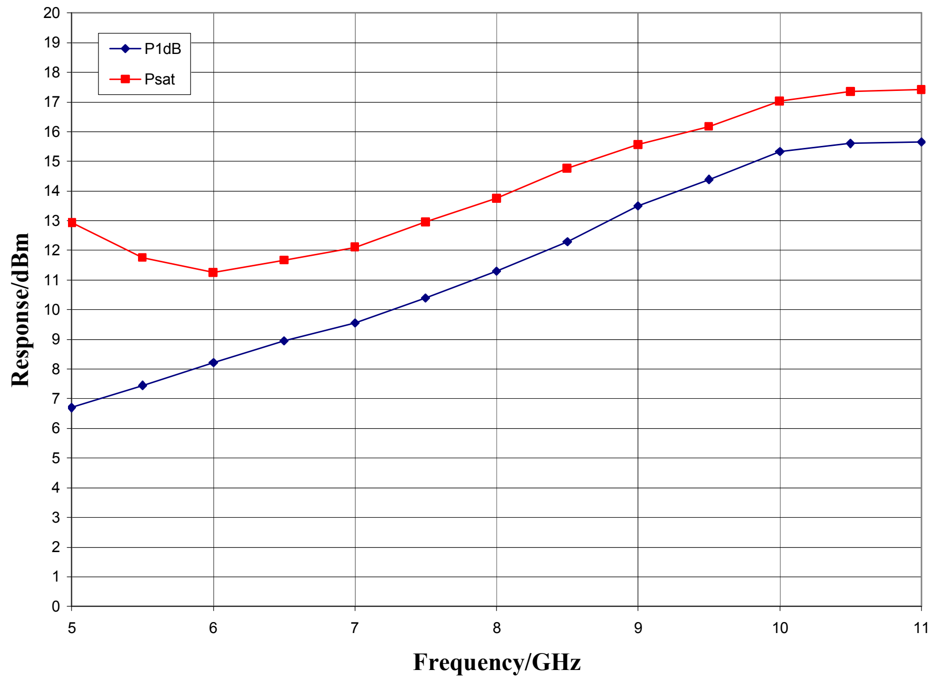
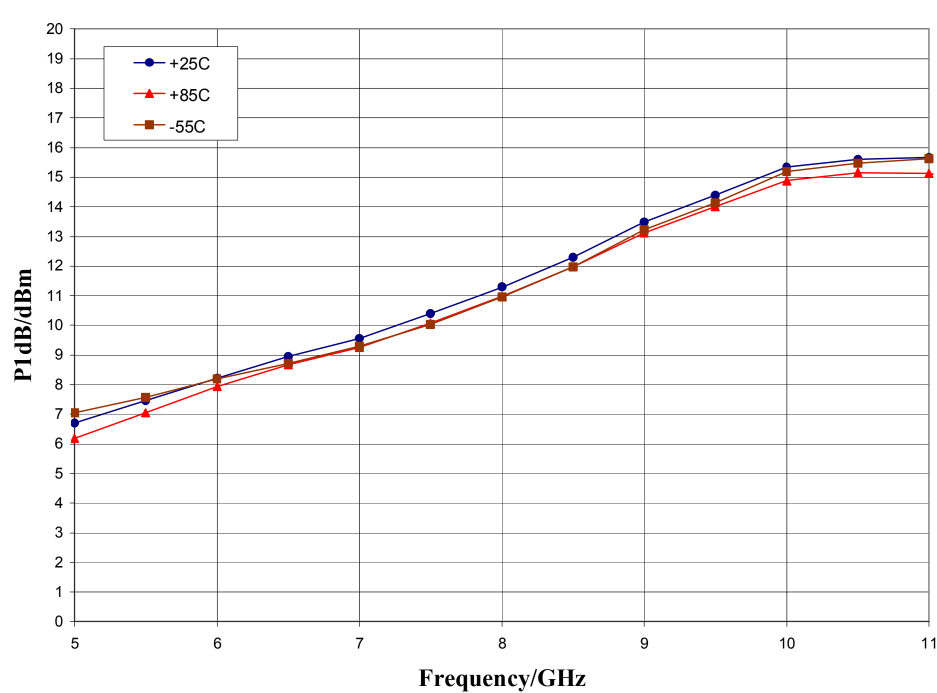
Typical Performance

Output Power, V_{dd} = 4 V, T_A = 25 °C



P1dB vs. Temperature, V_{dd} = 4 V



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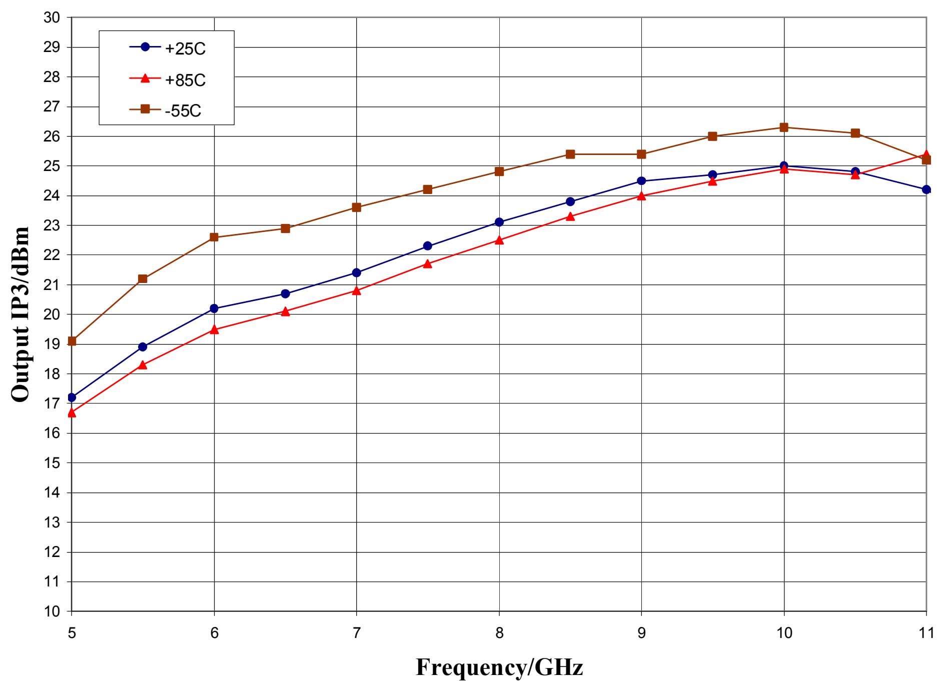
Typical Performance

Output IP3 vs. Temperature, V_{dd} = 4 V



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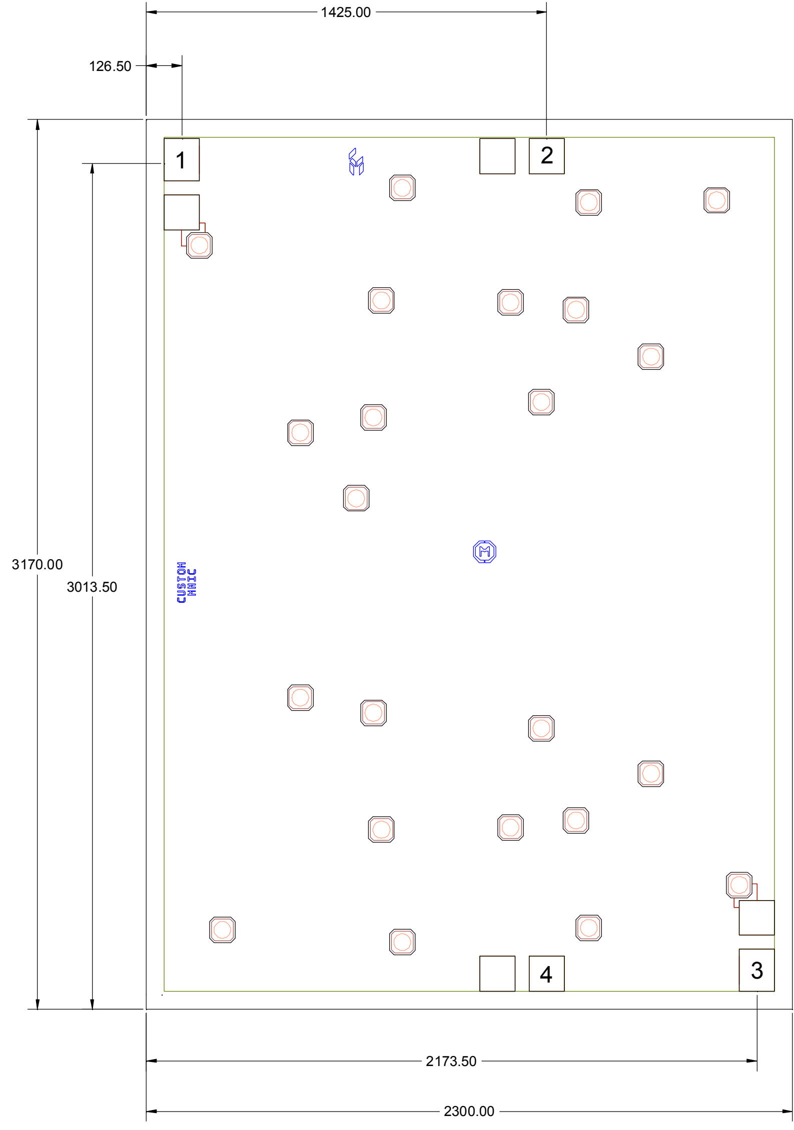
Mechanical Information

Die Outline (all dimensions in microns)



Notes:

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads are 100 microns square

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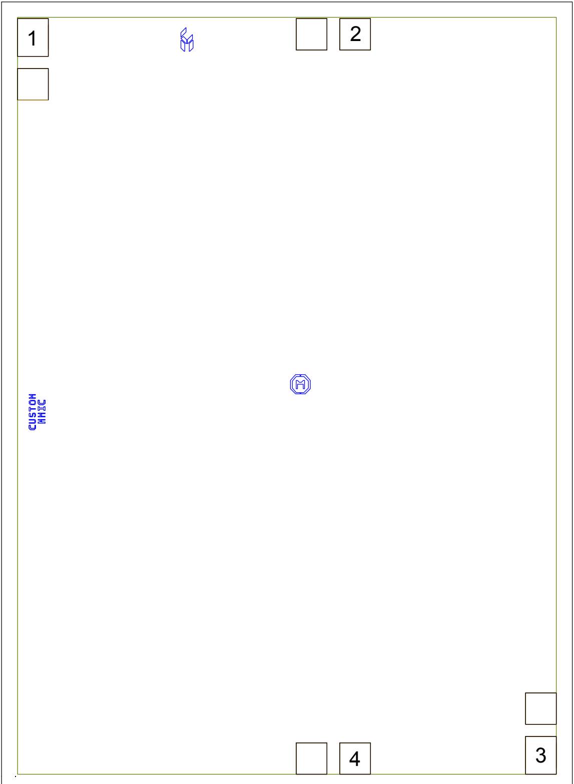
Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	RF in
2, 4	Vdd, Vdd-Optional	Power supply voltage Decoupling and bypass caps required. Only one of these pads needs to be connected to DC power supply.	Vdd
3	RF out	DC blocked and 50 ohm matched	RF out
Backside	Ground	Connect to RF / DC ground	GND

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Applications Information

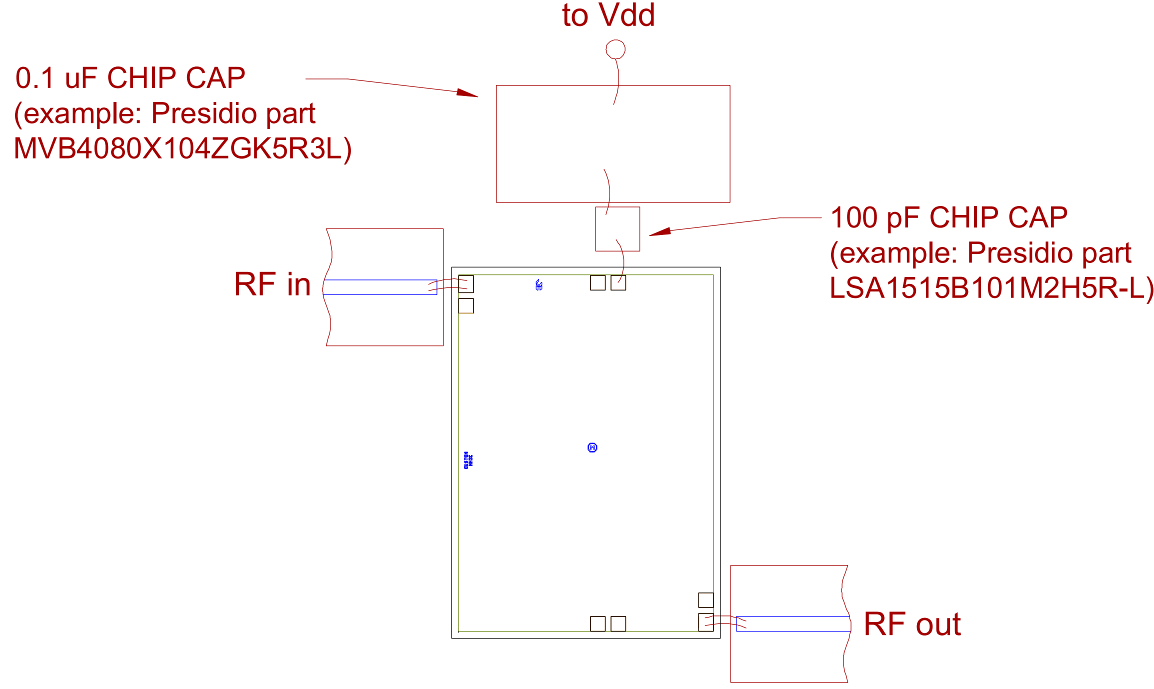
Assembly Guidelines

The backside of the CMD222 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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Applications Information

Biasing and Operation

The CMD 222 is biased with a positive drain supply. Performance is optimized when the drain voltage is set to +4 V, though it may be set to a minimum of +2.0 V and a maximum of +5 V.

Turn ON procedure:

1.Apply drain voltage V_{dd} and set to +4 V

Turn OFF procedure:

1.Turn off drain voltage V_{dd}

RF power can be applied at any time.

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